

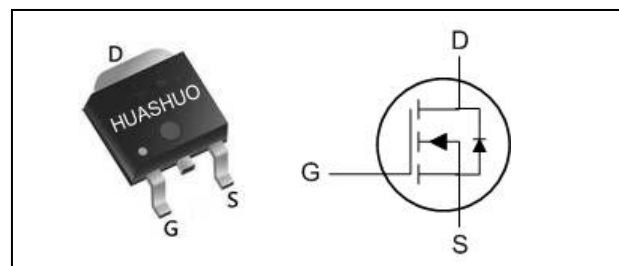
Description

The HSU0096 uses SGT technology to provide excellent $R_{DS(on)}$, low gate charge and fast switching characteristics. This device is suitable for use as a wide variety of applications.

- 100% EAS Guaranteed
- Low $R_{DS(on)}$
- Low Gate Charge
- RoHs and Halogen-Free Compliant

Product Summary

V_{DS}	100	V
$R_{DS(ON),TYP}$	8.7	m Ω
I_D	60	A

TO-252 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current ¹	60	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current ¹	38	A
I_{DM}	Pulsed Drain Current ²	240	A
EAS	Single Pulse Avalanche Energy ³	90	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	73	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.7	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	8.7	11	mΩ
	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =10A	---	11	14	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =100V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V, V _{DS} =0V	---	---	± 100	nA
Q _g	Total Gate Charge (10V)	V _{DS} =50V, V _{GS} =10V, I _D =20A	---	26	---	nC
Q _{gs}	Gate-Source Charge		---	4.3	---	
Q _{gd}	Gate-Drain Charge		---	6.7	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω, I _D =20A	---	7.5	---	ns
T _r	Rise Time		---	14	---	
T _{d(off)}	Turn-Off Delay Time		---	31	---	
T _f	Fall Time		---	26	---	
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	1410	---	pF
C _{oss}	Output Capacitance		---	495	---	
C _{rss}	Reverse Transfer Capacitance		---	16	---	

Diode Characteristics

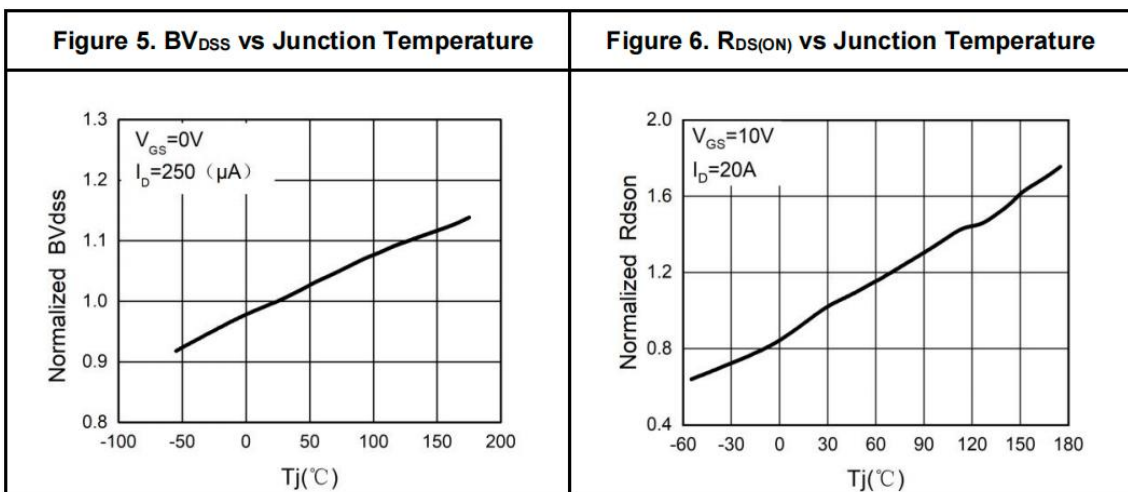
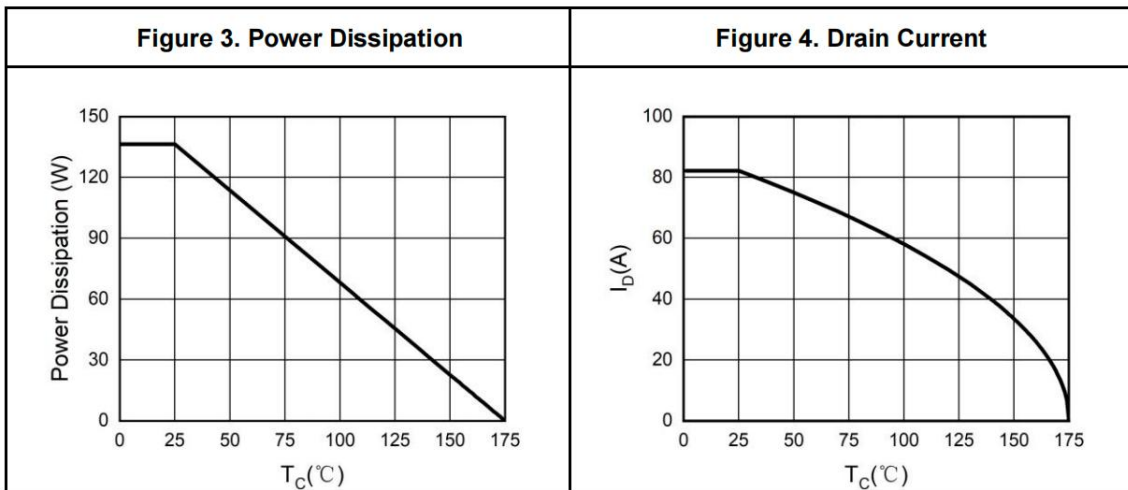
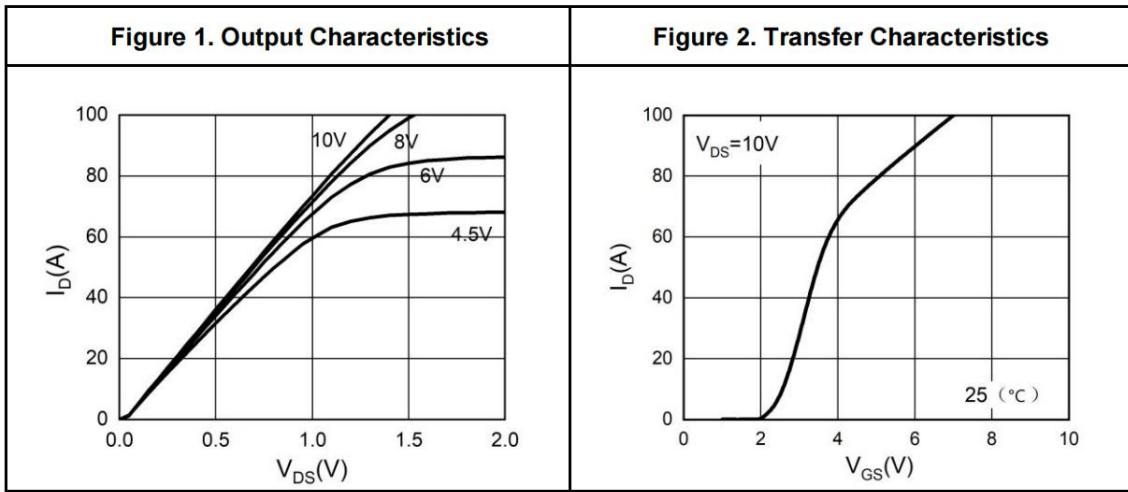
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	60	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, di/dt=100A/μs, T _J =25°C	---	43	---	nS
Q _{rr}	Reverse Recovery Charge		---	35	---	nC

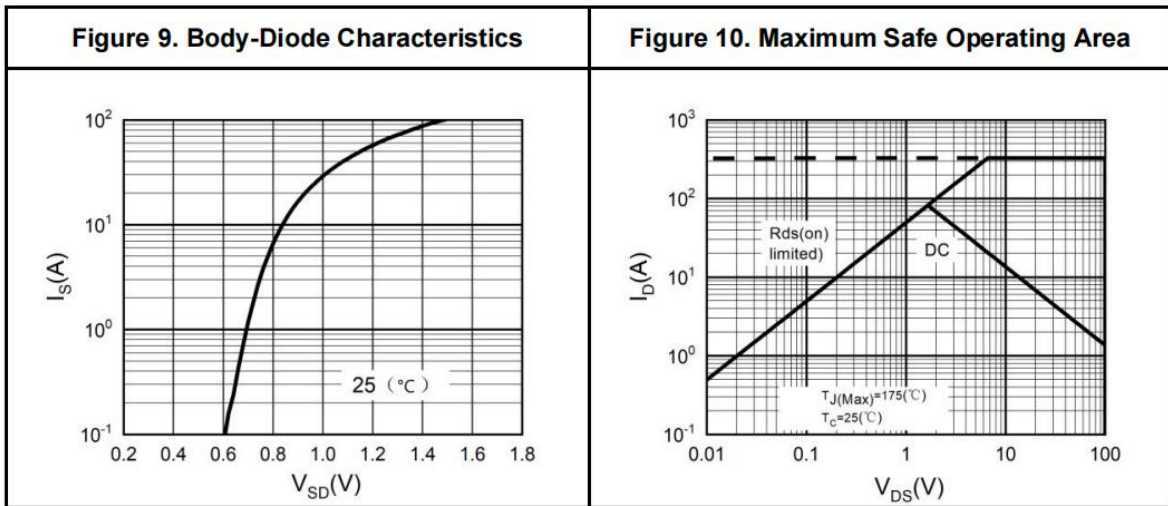
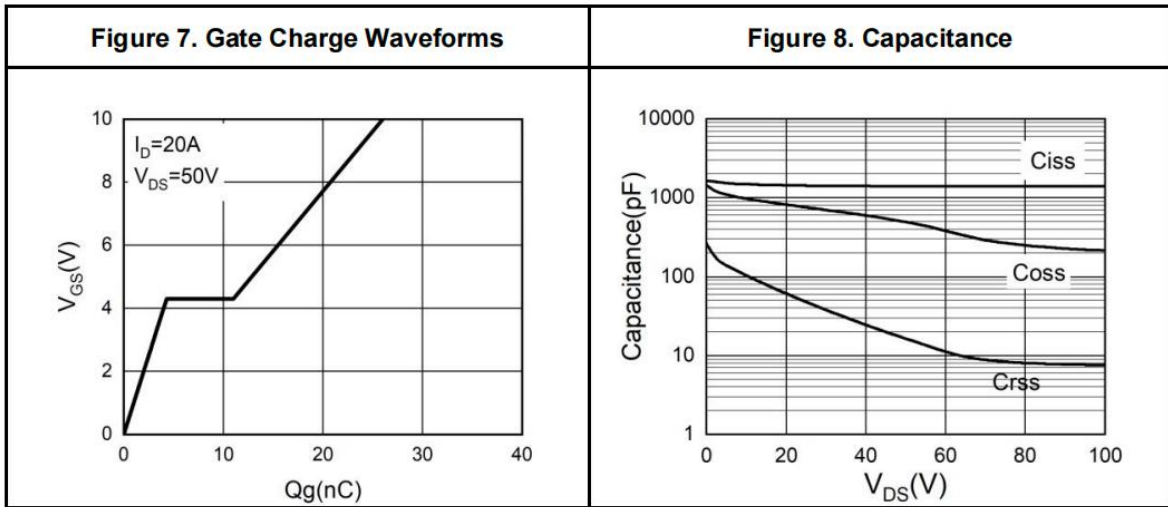
Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_G=25Ω
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



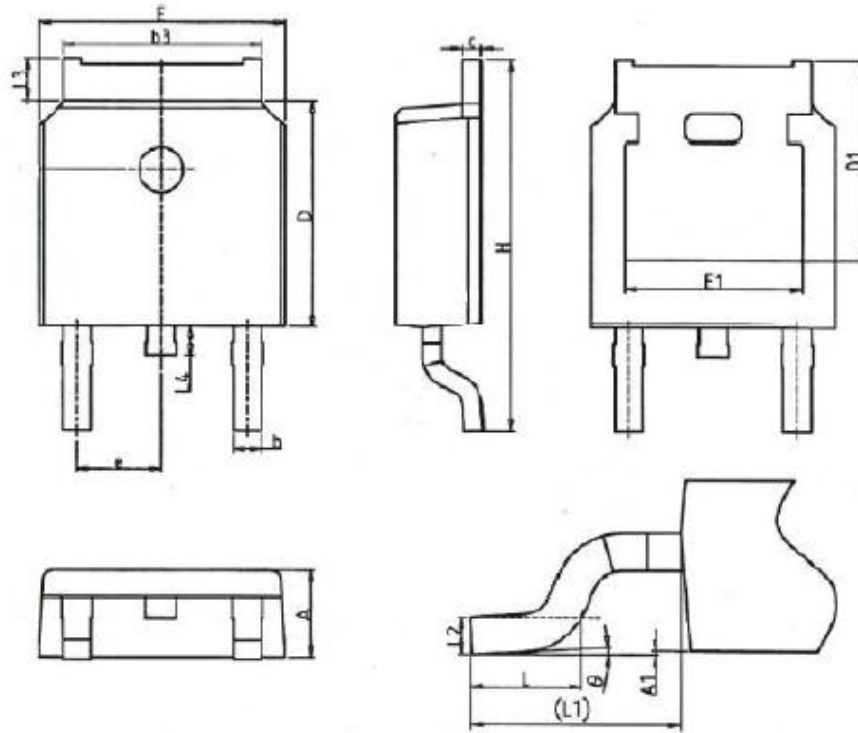
Typical Characteristics







TO252-2L Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.095
A1	-	0.2	-	0.008
b	0.68	0.9	0.026	0.036
b3	4.95	5.46	0.194	0.215
c	0.43	0.89	0.017	0.035
D	5.97	6.22	0.235	0.245
D1	5.300REF		0.209REF	
E	6.35	6.73	0.250	0.265
E1	4.32	--	0.170	-
e	2.286BSC		0.09BSC	
H	9.4	10.5	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.90REF		0.114REF	
L2	0.51BSC		0.020BSC	
L3	0.88	1.28	0.034	0.050
L4	0.5	1	0.019	0.039
θ	0°	8°	0°	8°